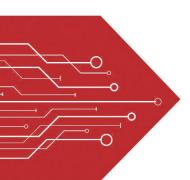
MSKSEMI















ESD

TVS

TSS

MOV

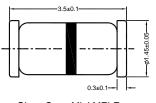
GDT

PLED

Brodnet data speet

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These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.



Glass Case Mini MELF Dimensions in mm

LL-34

REEL SPECIFICATION

P/N	PKG	QTY
LLDB3/LLDB4	LL34	2500

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Power Dissipation (T _a = 65 °C)	P _{tot}	150	mW
Repetitive Peak On-state Current (tp = 20 µs, f = 100 Hz)	I _{TRM}	2	А
Operating Junction and Storage Temperature Range	T_{j},T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
	LDB3	- V _{BO}	28	36	V
at C = 22 nF, see diagram 1	LDB4		35	45	
Breakover Voltage Symmetry at C = 22 nF, see diagram 1		$[+V_{BO} \text{-} \text{-}V_{BO}]$	-	3	V
Dynamic Breakover Voltage at $\Delta I = [I_{BO} \text{ to } I_F = 10 \text{ mA}]$		ΔV ±	5	ı	V
Output Voltage See diagram 2		Vo	5	ı	V
Breakover Current at C = 22 nF		I _{BO}	-	50	μΑ
Leakage Current at $V_B = 0.5 V_{BO}$ max		I_{B}	-	10	μΑ
Rise Time See diagram 3		t _r	-	2	μs



Diagram 1: Current-voltage characteristics

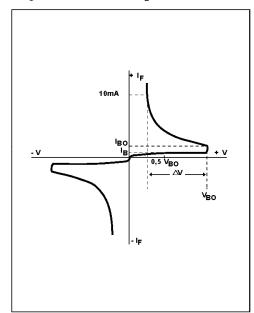


Diagram 2: Test circuit for output voltage

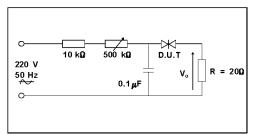


Diagram 3: Test circuit see diagram 2. Adjust R for Ip=0.5A

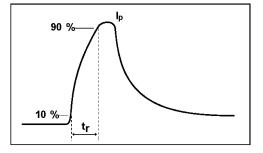


Fig. 1: Power dissipation versus ambient temperature (maximum values)

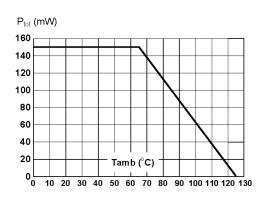


Fig. 2: Relative variation of V_{BO} versus junction temperature (typical values)

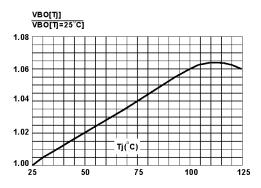
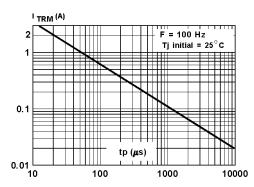


Fig. 3: Peak pulse current versus pulse duration (maximum values)





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